

[Document Name] Specification

[Title of Invention] An Evaluation Method using a TEG, A Method of manufacturing a Semiconductor Device Having the TEG, An Element Substrate and A Panel Having the TEG, A Program for Controlling Dosage and A computer-Readable Recording Medium recording the Program

[Scope of Claims]

[Claim 1]

An evaluation method of a TFT characterized by

a step of forming a TEG and the TFT over a same substrate, each having a gate electrode over a semiconductor film which is formed to have a low concentration impurity region overlapping the gate electrode,

a step of measuring resistance of the low concentration impurity region of the TEG, and

estimating an impurity concentration of the low concentration impurity region of the TFT by the resistance.

[Claim 2]

An evaluation method of a TFT characterized by

a step of forming a TEG and the TFT over a same substrate, each having a gate electrode that is laminated with a first conductive film and a second conductive film over a semiconductor film which has a low concentration impurity region overlapping the gate electrode,

a step of measuring resistance of the low concentration impurity region of the TEG, and

estimating an impurity concentration of the low concentration impurity region of the TFT by the resistance